# ICSI-7

# 7th International Conference on Silicon Epitaxy and Heterostructures



May 22(Sun) - 26(Thu), 2011
Research Institute of Electrical Communication,
Tohoku Univ., Sendai, Japan

Web site: http://www.murota.riec.tohoku.ac.jp/ICSI7/

The ICSI-7 will provide a unique forum for reviewing and discussing novel developments in physics and device technologies of Si epitaxy, heterostructures, and nanostructures. The conference is a biannual succession of the previous ICSI conferences (1st: Miyagi Zao, Japan, 1999; 2nd: Strasbourg, France, 2001; 3rd: Santa Fe, USA, 2003; 4th: Awaji Island, Japan, 2005; 5th: Marseille, France, 2007; 6th: Los Angeles, USA, 2009).

NOTE: 6th Int. Symp. on Control of Semiconductor Interfaces (ISCSI-VI, May 25(Wed)-27(Fri), 2011) & some workshops will be held successively. Some focus sessions will be joint with ISCSI-VI.

#### **CONFERENCE TOPICS**

- Growth, Characterization and Modeling of Si and Group IV (C, Si, Ge, Sn) based Thin Film Materials including research on various interfaces on Si;
- Formation and Characterization of Group IV based Nanostructures including quantum dots, nanowires and self-assembly processes;
- · Process Technologies for Group IV based Heterostructures including doping,
- Source/drain and channel engineering as well as strained Si;
- · Electronic Properties and Device Applications such as transistors and nano-structured devices;
- Optical Properties and Device Applications including solar cells of Si and Ge based heterostructures;
- · Germanium based semiconductor... from materials to devices;
- Si(Ge)-based materials growth and device fabrication for spintronics such as spin polarized electron injection, transport, and manipulation, as well as other electron spin based phenomena;
- Growth, characterization and applications of epitaxial (high-k) dielectric materials;
- Emerging technologies: Hetero-Epitaxial film growths on SiGe and characterization (Graphene, III-V and others materials).

The Organizers welcome you to ICSI-7 at Sendai, Japan.

Shigeaki Zaima (Chair)
Nagoya University, Japan
Junichi Murota (Vice Chair)
Tohoku University, Japan
Seiichi Miyazaki (Vice Chair)
Nagoya University, Japan

### ABSTRACT SUBMISSION Deadline: FEBRUARY 15, 2011 (Extended)

**PDF** or **MS** Word file of Camera-ready **two-page** abstract (one-page main text and one-page figures), written in English on white bond paper (A4 size; 2.5cm margin on four sides), should be prepared. We will announce later how to submit the abstract on this web site. The abstract is strongly recommended to be prepared in **Black/White**. (Abstracts will be published in Black/White). The abstract should be headed by the title, author(s), affiliation(s), address, telephone number, fax number and e-mail address, and clearly describe the originality and new contributions of the work. Proceedings will be published in the special issue of **Thin Solid Films** (manuscript submission deadline will be around **middle of May, 2011**). Detailed information will be announced on the above symposium web site.

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